

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition
1	BRS	365	((rpm or "revolution per minute") same (liquid or water) same (wafer or substrate) same (rins\$3 or wash\$3)) and @pd<=19980618	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/11 12:10		0
2	BRS	1850	((rpm or "revolution per minute") neat5 low) same (liquid or water) same (wafer or substrate) same (rins\$3 or wash\$3)	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/11 10:52		0
3	BRS	18	((rpm or "revolution per minute") near5 low) same (liquid or water) same (wafer or substrate) same (rins\$3 or wash\$3)	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/11 11:28		0
4	BRS	7	(post adj etching) same rins\$3 same (semiconductor or wafer or substrate)	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/11 11:29		0
5	BRS	7	(post adj cleaning) same rins\$3 same (semiconductor or wafer or substrate)	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/11 11:36		0
6	BRS	7944	(rins\$3 or immers\$3) same wafer	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/11 12:10		0
7	BRS	3549	(rins\$3 or immers\$3) same wafer same (water)	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/11 12:11		0
8	BRS	2133	((rins\$3 or immers\$3) same wafer same (water)) and @pd<=19980618	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/11 12:14		0
9	BRS	66	(rins\$3 or immers\$3) same wafer same (water) same (plasma adj etch\$3)	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/11 12:13		0
10	BRS	35	((rins\$3 or immers\$3) same wafer same (water) same (plasma adj etch\$3)) and @pd<=19980618	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/11 12:15		0